

**CLEAN VERSION OF AMENDED SPECIFICATION PARAGRAPHS****ELECTROSTATIC DISCHARGE PROTECTION DEVICE**

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**The paragraph beginning at page 6, line 6:**

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Figure 3 is a novel ESD protection device according to the invention. Device 300 includes a substrate 302 having a first doped (source) region 304 and a second doped (drain) region 306. First doped region 304 and second doped region 306 are separated by only a region 311 of substrate 302. In one embodiment, substrate 302 has a p-type conductivity material, and first and second doped regions 304 and 306 have an n-type conductivity material. First and second doped regions 304 and 306 have a higher doping concentration than the doping concentration of substrate 302. In other words, substrate 302 is lightly doped (indicated by p-) and first and second doped regions 304 and 306 are heavily doped (indicated by n+). In addition, first doped region 304 can be connected to a ground at node 320. Those of ordinary skill in the art can readily recognize that first doped region 304 can also be connected to a voltage source or a power source. Second doped region 306 can be connected to an external bonding pad 312. Furthermore, since device 300 of Figure 3 includes no gate structure above the first and second doped regions 304 and 306, it is a gateless ESD protection device.